

Attorney Docket No. **10113231**

**PATENT**

Date: **November 26, 2003**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

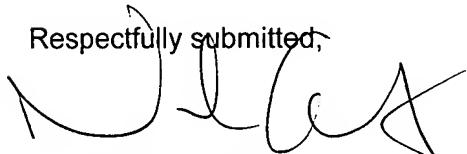
**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 CFR §1.97 and §1.98**

Sir:

The references cited on the attached Form PTO/SB/08A & B (modified) are being called to the attention of the Examiner. Copies of cited U.S. patents and U.S. patent application publications are not enclosed, as permitted for U.S. application filed after June 30, 2003 (Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Application Filed After June 30, 2003, Pre-OG Notices). Copies of foreign references and articles are enclosed. It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

Some documents may have markings on thereon. No significance is meant to be attached to the markings. Furthermore, as provided for by 37 CFR §1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information. Translations of foreign documents are not verified.

Respectfully submitted,



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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>					<b>Complete if Known</b>			
					Application Number			
					Filing Date			
					First Named Inventor		<b>Chih-Yuan HSIAO</b>	
					Art Unit			
					Examiner Name			
Sheet	1	of	1	Attorney Docket Number	<b>10113231</b>			

<b>U.S. PATENT DOCUMENTS</b>						
Examiner Initials	Cite No.	Document Number (Number – kind code)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Passages or Relevant Figures Appear	
	A1	US 6,432,774 B2	08/13/2002	Heo et al		
	A2	5,519,236	05/21/1996	Ozaki		
	A3					
	A4					
	A5					
	A6					
	A7					

<b>FOREIGN PATENT DOCUMENTS</b>						
Examiner Initials	Cite No.	Document Number (Number – kind code)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Passages or Relevant Figures Appear	T
	B1					
	B2					
	B3					
	B4					

<b>OTHER PRIOR ART</b>						
Examiner Initials	Cite No.	Include name of author (in CAPS), 'title of article' (when appropriate), <i>title of the item</i> (book, magazine, symposium, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published				T
	C1	DEBRA S. WOOLSEY, 'Enhanced discrete DMOS power trench gate oxide growth', <i>Solid State Technology</i> , Volume 45, Issue 8, August 2002, Pennwell Publishing, US				
	C2					
	C3					
	C4					
	C5					